New Jersey Semi-Conductor Products, Inc.

20 STERN AVE. SPRINGFIELD, NEW JERSEY 07081 U.S.A.

D40C Series

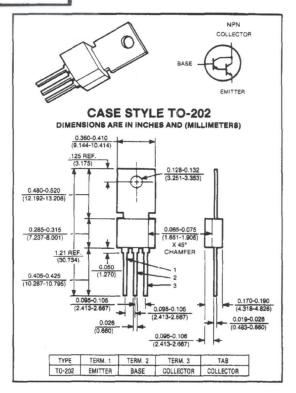
TELEPHONE: (973) 376-2922 (212) 227-6005 FAX: (973) 376-8960

30-50 VOLTS .5 AMP, 6.25 WATTS

Designed for driver, regulator, touch switch, I.C. driver, audio output, relay substitute, oscillator, servo-amplifier, and capacitor multiplier applications.

Features:

- hFE Min. 10,000 and 40,000
- 1.33 Watt power dissipation at T_A = 25°



maximum ratings (T_A = 25°C) (unless otherwise specified)

RATING	SYMBOL	D40C1	D40C4	D40C7	UNITS
Collector-Emitter Voltage	VCEO	30	40	50	Volts
Collector-Emitter Voltage	VCES	30	40	50	Volts
Emitter Base Voltage	VEBO	13	13	13	Volts
Collector Current — Continuous Peak ⁽¹⁾	IC ICM	.5 1.0	.5 1.0	.5 1.0	A
Base Current — Continuous	IB	0.1	0.1	0.1	A
Total Power Dissipation @ T _A = 25°C @ T _C = 25°C	PD	1.33 6.25	1.33 6.25	1.33 6.25	Watts
Operating and Storage Junction Temperature Range	T _J , T _{STG}	-55 to +150	-55 to +150	-55 to +150	°C

thermal characteristics

Thermal Resistance, Junction to Ambient	R _{ØJA}	75	75	75	°C/W
Thermal Resistance, Junction to Case	R _{ØJC}	20	20	20	°C/W
Maximum Lead Temperature for Soldering	T	060	000	000	
Purposes: 1/8" from Case for 5 Seconds		260	260	260	°C

(1) Pulse Test: Pulse Width = 300ms. Duty Cycle \leq 2%.



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

Quality Semi-Conductors

electrical characteristics ($T_C = 25^{\circ}C$) (unless otherwise specified)

CHARACTERISTIC		SYMBOL	MIN	TYP	MAX	UNIT
ff characteristics(1)						
Collector-Emitter Voltage (I _C = 10mA)	D40C1 D40C4 D40C7	VCEO	30 40 50			Volts
Collector Cut-off Current (V _{CE} = Rated V _{CES})	(T _C = 25°C) (T _C = 150°C)	ICES ICBO		_	0.5 20	μA
Emitter Cutoff Current (V _{EB} = 13V)		I _{EBO}		_	0.1	μA
econd breakdown Second Breakdown with Base Forward Biased		FBSOA		SEE FI	GURE 2	
Second Breakdown with Base Forward Biased		FBSOA		SEE FI	GURE 2	
		FBSOA h _{FE}	10K	SEE FI	GURE 2 60K	
Second Breakdown with Base Forward Biased on characteristics DC Current Gain			10K	SEE FI		v

dynamic characteristics

Collector Capacitance (V _{CE} = 10V, f = 1MHz)	C _{CBO}	-	-	220	pF
Current Gain - Bandwidth Product (I _C = 20mA, V _{CE} = 5V)	fT	-	75	-	MHz

switching characteristics

Resistive Load						
Delay Time + Rise Time	I _C = 1A, I _{B1} = I _{B2} = 1mA	t _d + t _r	-	100		ns
Storage Time	V_{CC} = 30V, t_p = 25 μ sec	ts	-	350	-	
Fall Time		t _f	-	800	-	

(1) Pulse Test: PW \leq 300ms Duty Cycle \leq 2%.

